

LBAS16TW1T1G SURFACE MOUNT FAST SWITCHING DIODE

Features

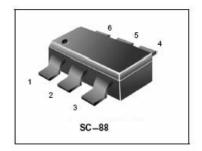
Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Also Available in Lead Free Version

 S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Pb-Free package is available

DEVICE MARKING
[LBAS16TW1T1G=KA2]







Maximum Ratings @ TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V	
RMS Reverse Voltage	V _{R(RMS)}	53	V	
Forward Continuous Current (Note 1)	I _{FM}	300	mA	
Average Rectified Output Current (Note 1)	Io	150	mA	
Non-Repetitive Peak Forward Surge Current @ t = 1.0µs @ t = 1.0s	I _{FSM}	2.0 1.0	А	
Power Dissipation (Note 1)	P _d	200	mW	
Thermal Resistance Junction to Ambient Air (Note 1)	R ₀ JA	625	°C/W	
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C	

Electrical Characteristics @ T_A = 25°C unless otherwise specified

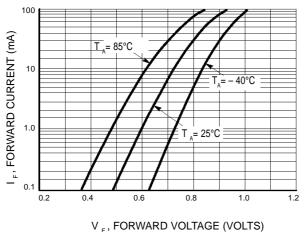
Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 2)	V _{(BR)R}	75	_	V	$I_R = 1\mu A$
Forward Voltage (Note 2)	VF	_	0.715 0.855 1.0 1.25	V	I _F = 1.0mA I _F = 10mA I _F = 50mA I _F = 150mA
Reverse Current (Note 2)	I _R	_	1.0 50 30 25	μΑ μΑ μΑ nA	$V_R = 75V$ $V_R = 75V$, $T_j = 150^{\circ}C$ $V_R = 25V$, $T_j = 150^{\circ}C$ $V_R = 20V$
Total Capacitance	C _T	_	2.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	_	4.0	ns	$I_F = I_R = 10 \text{mA},$ $I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$

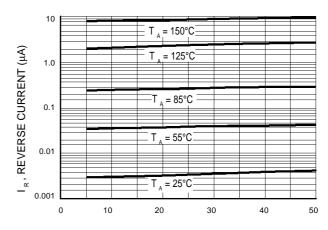
Notes

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. Short duration test pulse used to minimize self-heating effect.



LBAS16TW1T1G, S-LBAS16TW1T1G

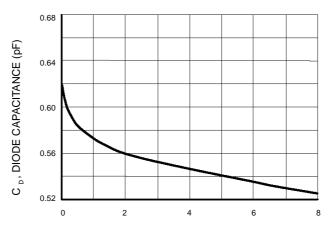




F, FORWARD VOLIAGE (VOLIS)

Figure 2. Forward Voltage

 V_R , REVERSE VOLTAGE (VOLTS) Figure 3. Leakage Current



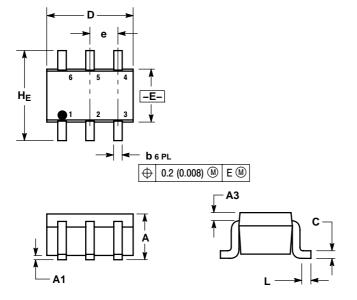
 V_R , REVERSE VOLTAGE (VOLTS)

Figure 4. Capacitance



LBAS16TW1T1G, S-LBAS16TW1T1G

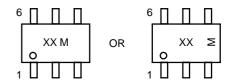
SC-88



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.95	1.10	0.031	0.037	0.043	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A3	0.20 REF			0.008 REF			
b	0.10	0.21	0.30	0.004	0.008	0.012	
С	0.10	0.14	0.25	0.004	0.005	0.010	
D	1.80	2.00	2.20	0.070	0.078	0.086	
E	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65 BSC			0.026 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
He	2.00	2.10	2.20	0.078	0.082	0.086	

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

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